CY62136ESL MoBL®

2-Mbit (128 K × 16) Static RAM

Features

- Very high speed: 45 ns
- Wide voltage range: 2.2 V to 3.6 V and 4.5 V to 5.5 V
- Ultra low standby power
  - Typical standby current: 1 µA
  - Maximum standby current: 7 µA
- Ultra low active power
  - Typical active current: 2 mA at f = 1 MHz
- Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features
- Automatic power-down when deselected
- Complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Available in Pb-free 44-pin thin small outline package (TSOP) II package

Functional Description

The CY62136ESL is a high performance CMOS static RAM organized as 128K words by 16 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications. The device also has an automatic power down feature that reduces power consumption when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ($\overline{CE}$ HIGH). The input and output pins (I/O_0 through I/O_{15}) are placed in a high impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH) or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW).

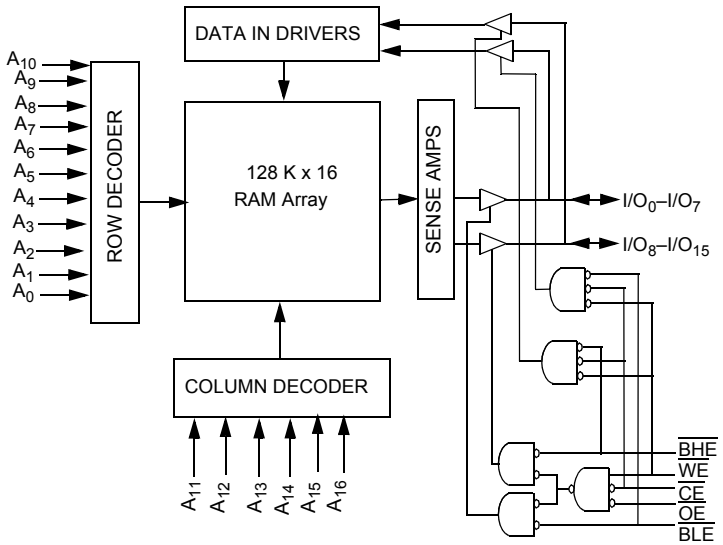
To write to the device, take Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7) is written into the location specified on the address pins (A_0 through A_{16}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{16}).

To read from the device, take Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins appears on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory appears on I/O_8 to I/O_{15}. See the Truth Table on page 11 for a complete description of read and write modes.

The device is suitable for interfacing with processors that have TTL I/P levels. It is not suitable for processors that require CMOS I/P levels. Please see Electrical Characteristics on page 4 for more details and suggested alternatives.

For a complete list of related documentation, click here.

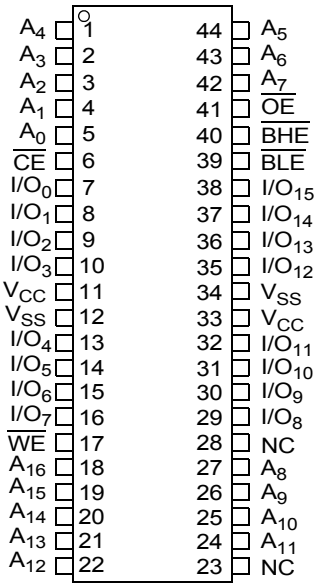
Logic Block Diagram



Contents

Pin Configuration

Figure 1. 44-pin TSOP II pinout (Top View) [1]



Product Portfolio

Product	Range	V_{CC} Range (V) [2]	Speed (ns)	Power Dissipation					
				Operating I_{CC}, (mA)				Standby, I_{SB2} (µA)	
				f = 1MHz		f = f_{max} =1/TRC			
				Typ [3]	Max	Typ [3]	Max	Typ [3]	Max
CY62136ESL	Industrial	2.2 V to 3.6 V and 4.5 V to 5.5 V	45	2	2.5	15	20	1	7

Notes
1. NC pins are not connected on the die.
2. Datasheet specifications are not guaranteed for V_{CC} in the range of 3.6 V to 4.5 V.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V, and V_{CC} = 5 V, T_A = 25 °C.

Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature ..... –65 °C to +150 °C

Ambient temperature with power applied ..... –55 °C to +125 °C

Supply voltage to ground potential [4, 5] .....–0.5 V to 6.0 V

DC voltage applied to outputs in High Z State [4, 5] .....–0.5 V to 6.0 V

DC input voltage [4, 5] .....–0.5 V to 6.0 V

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) .....>2001 V

Latch up current .....> 200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC}[6]
CY62136ESL	Industrial	–40 °C to +85 °C	2.2 V–3.6 V, and 4.5 V–5.5 V

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		45 ns			Unit
				Min	Typ [7]	Max	
V_{OH}	Output HIGH voltage	$2.2 \le V_{CC} \le 2.7$	I_{OH} = –0.1 mA	2.0	–	–	V
		$2.7 \le V_{CC} \le 3.6$	I_{OH} = –1.0 mA	2.4	–	–	
		$4.5 \le V_{CC} \le 5.5$	I_{OH} = –1.0 mA	2.4	–	–	
		$4.5 \le V_{CC} \le 5.5$	I_{OH} = –0.1 mA	–	–	3.4 [8]	
V_{OL}	Output LOW voltage	$2.2 \le V_{CC} \le 2.7$	I_{OL} = 0.1 mA	–	–	0.4	V
		$2.7 \le V_{CC} \le 3.6$	I_{OL} = 2.1 mA	–	–	0.4	
		$4.5 \le V_{CC} \le 5.5$	I_{OL} = 2.1 mA	–	–	0.4	
V_{IH}	Input HIGH voltage	$2.2 \le V_{CC} \le 2.7$		1.8	–	V_{CC} + 0.3	V
		$2.7 \le V_{CC} \le 3.6$		2.2	–	V_{CC} + 0.3	
		$4.5 \le V_{CC} \le 5.5$		2.2	–	V_{CC} + 0.5	
V_{IL}	Input LOW voltage	$2.2 \le V_{CC} \le 2.7$		–0.3	–	0.6	V
		$2.7 \le V_{CC} \le 3.6$		–0.3	–	0.8	
		$4.5 \le V_{CC} \le 5.5$		–0.5	–	0.8	
I_{IX}	Input leakage current	$GND \le V_{in} \le V_{CC}$		–1	–	+1	µA
I_{OZ}	Output leakage current	$GND \le V_O \le V_{CC}$, Output disabled		–1	–	+1	µA
I_{CC}	V_{CC} Operating supply current	$f = f_{max} = 1/t_{RC}$	$V_{CC} = V_{CCmax}$, I_{OUT} = 0 mA, CMOS levels	–	15	20	mA
		f = 1 MHz		–	2	2.5	
I_{SB1}[9]	Automatic CE power-down current — CMOS inputs	$\overline{CE} \ge V_{CC}$ – 0.2 V, $V_{IN} \ge V_{CC}$ – 0.2 V or $V_{IN} \le$ 0.2 V, f = f_{max} (Address and data only), f = 0 ($\overline{OE}$, $\overline{BHE}$, $\overline{BLE}$ and $\overline{WE}$), $V_{CC} = V_{CC(max)}$		–	1	7	µA
I_{SB2}[9]	Automatic CE power-down current — CMOS inputs	$\overline{CE} \ge V_{CC}$ – 0.2 V, $V_{IN} \ge V_{CC}$ – 0.2 V or $V_{IN} \le$ 0.2 V, f = 0, $V_{CC} = V_{CC(max)}$		–	1	7	µA

Notes

4. V_{IL}(min) = –2.0 V for pulse durations less than 20 ns.
5. V_{IH}(max) = V_{CC} + 0.75 V for pulse durations less than 20 ns.
6. Full Device AC operation assumes a 100 µs ramp time from 0 to V_{CC} (min) and 200 µs wait time after V_{CC} stabilization.
7. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V, and V_{CC} = 5 V, T_A = 25 °C.
8. Please note that, the maximum V_{OH} limit for this device may not exceed minimum CMOS V_{IH} of 3.5 V. If you are interfacing this SRAM with 5 V legacy processors that require a minimum V_{IH} of 3.5 V, please refer to Application Note AN6081 for technical details and options you may consider. This maximum limit is not 100% tested.
9. Chip enable ($\overline{CE}$) and byte enables ($\overline{BHE}$ and $\overline{BLE}$) need to be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.

Capacitance

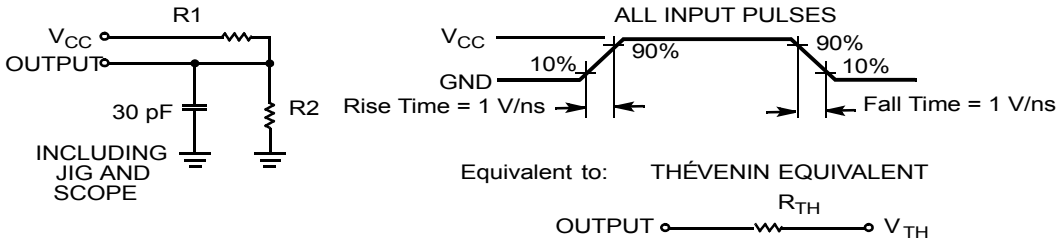
Parameter [10]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output capacitance		10	pF

Thermal Resistance

Parameter [10]	Description	Test Conditions	44-pin TSOP II	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Still Air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	57	°C/W
Θ_{JC}	Thermal resistance (junction to case)		17	°C/W

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms



Parameters	2.5 V	3.0 V	5.0 V	Unit
R1	16667	1103	1800	Ω
R2	15385	1554	990	Ω
R_{TH}	8000	645	639	Ω
V_{TH}	1.20	1.75	1.77	V

Note
10. Tested initially and after any design or process changes that may affect these parameters.

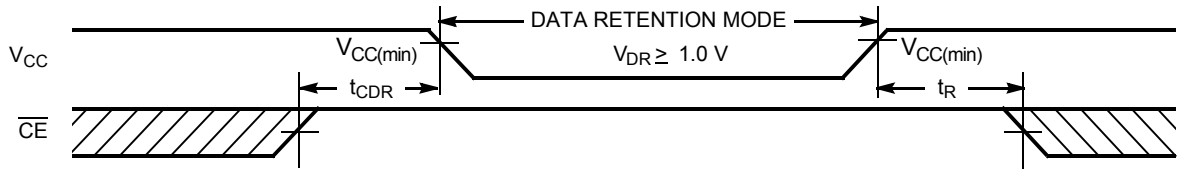
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions		Min	Typ [11]	Max	Unit
V_{DR}	V_{CC} for data retention			1.0	–	–	V
I_{CCDR} [12]	Data retention current	$\overline{CE} \geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V	V_{CC} = 1.0 V	–	0.8	3	µA
t_{CDR} [13]	Chip deselect to data retention time			0	–	–	ns
t_R [14]	Operation recovery time			45	–	–	ns

Data Retention Waveform

Figure 3. Data Retention Waveform



Notes

11. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, T_A = 25 °C.
12. Chip enable ($\overline{CE}$) and byte enables ($\overline{BHE}$ and $\overline{BLE}$) need to be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} specification. Other inputs can be left floating.
13. Tested initially and after any design or process changes that may affect these parameters.
14. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 100$ µs or stable at $V_{CC(min)} \geq 100$ µs.

Switching Characteristics

Over the Operating Range

Parameter [15, 16]	Description	45 ns		Unit
		Min	Max	
Read Cycle				
t_{RC}	Read cycle time	45	–	ns
t_{AA}	Address to data valid	–	45	ns
t_{OHA}	Data hold from address change	10	–	ns
t_{ACE}	$\overline{CE}$ LOW to data valid	–	45	ns
t_{DOE}	$\overline{OE}$ LOW to data valid	–	22	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z [17]	5	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z [17, 18]	–	18	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z [17]	10	–	ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z [17, 18]	–	18	ns
t_{PU}	$\overline{CE}$ LOW to power-up	0	–	ns
t_{PD}	$\overline{CE}$ HIGH to ower-down	–	45	ns
t_{DBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to data valid	–	22	ns
t_{LZBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to Low Z [17]	5	–	ns
t_{HZBE}	$\overline{BLE}$/$\overline{BHE}$ HIGH to High Z [17, 18]	–	18	ns
Write Cycle [19, 20]				
t_{WC}	Write cycle time	45	–	ns
t_{SCE}	$\overline{CE}$ LOW to write end	35	–	ns
t_{AW}	Address setup to write end	35	–	ns
t_{HA}	Address hold from write end	0	–	ns
t_{SA}	Address setup to write start	0	–	ns
t_{PWE}	$\overline{WE}$ pulse width	35	–	ns
t_{BW}	$\overline{BLE}$/$\overline{BHE}$ LOW to write end	35	–	ns
t_{SD}	Data setup to write end	25	–	ns
t_{HD}	Data hold from write end	0	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High Z [17, 18]	–	18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z [17]	10	–	ns

Notes

15. In an earlier revision of this device, under a specific application condition, READ and WRITE operations were limited to switching of the byte enable and/or chip enable signals as described in the Application Notes AN13842 and AN66311. However, the issue has been fixed and in production now, and hence, these Application Notes are no longer applicable. They are available for download on our website as they contain information on the date code of the parts, beyond which the fix has been in production.
16. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3 V, and output loading of the specified I_{OL}/I_{OH} as shown in the Figure 2 on page 5.
17. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
18. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
19. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$ or both = V_{IL}. All signals must be active to initiate a write and any of these signals can terminate a write by going inactive. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.
20. The minimum write cycle pulse width for Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ Controlled) should be equal to sum of t_{SD} and t_{HZWE}.

Switching Waveforms

Figure 4. Read Cycle No.1 (Address Transition Controlled) [21, 22]

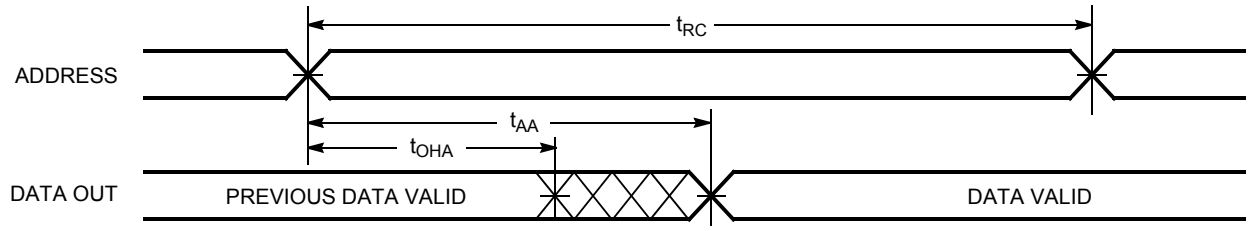
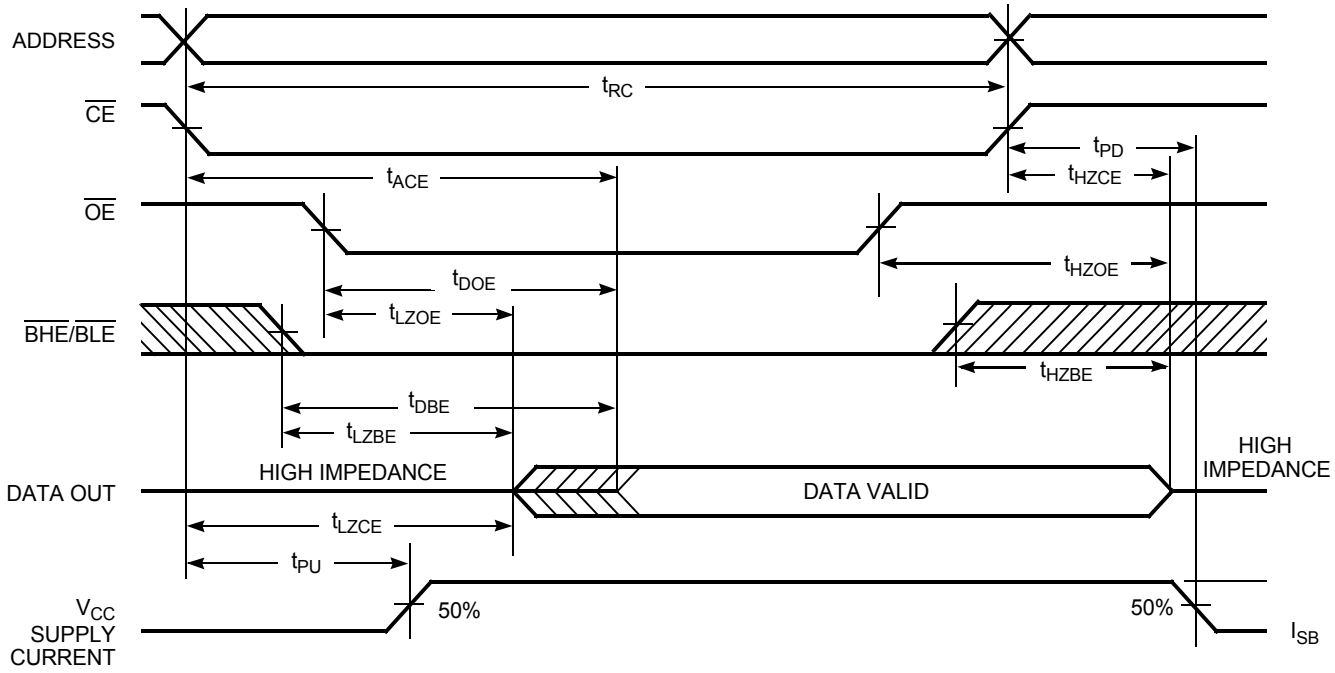


Figure 5. Read Cycle No. 2 ($\overline{OE}$ Controlled) [22, 23]



Notes
21. The device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$, or both = V_{IL}.
22. $\overline{WE}$ is HIGH for read cycle.
23. Address valid before or similar to $\overline{CE}$, $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms (continued)

Figure 6. Write Cycle No. 1 (WE Controlled) [24, 25, 26]

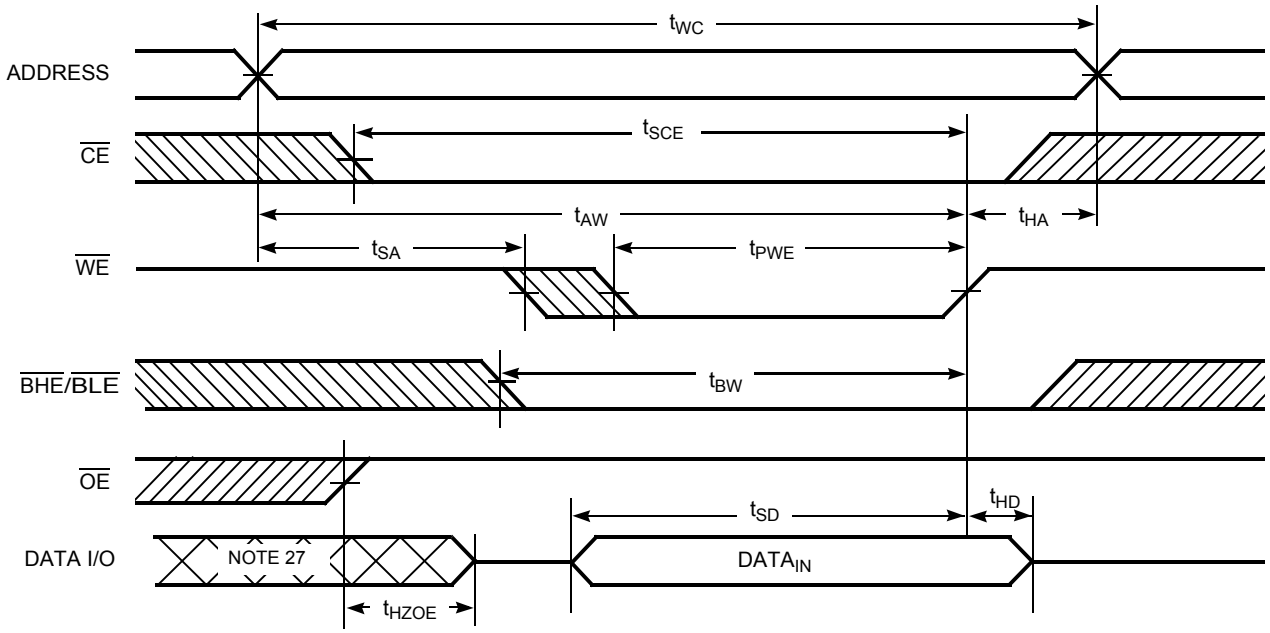
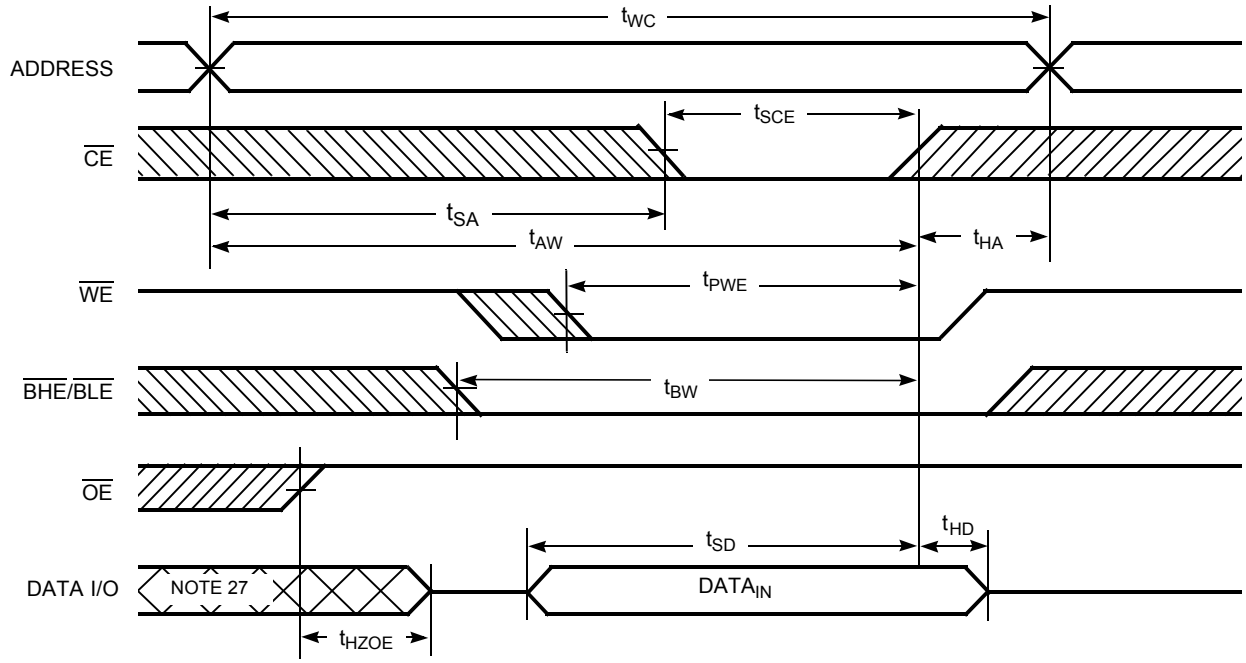


Figure 7. Write Cycle No. 2 (CE Controlled) [24, 25, 26]



Notes

24. The internal write time of the memory is defined by the overlap of WE, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals are ACTIVE to initiate a write and any of these signals terminate a write by going INACTIVE. The data input setup and hold timing are referenced to the edge of the signal that terminates the write.
25. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
26. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high impedance state.
27. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW) [28, 29]

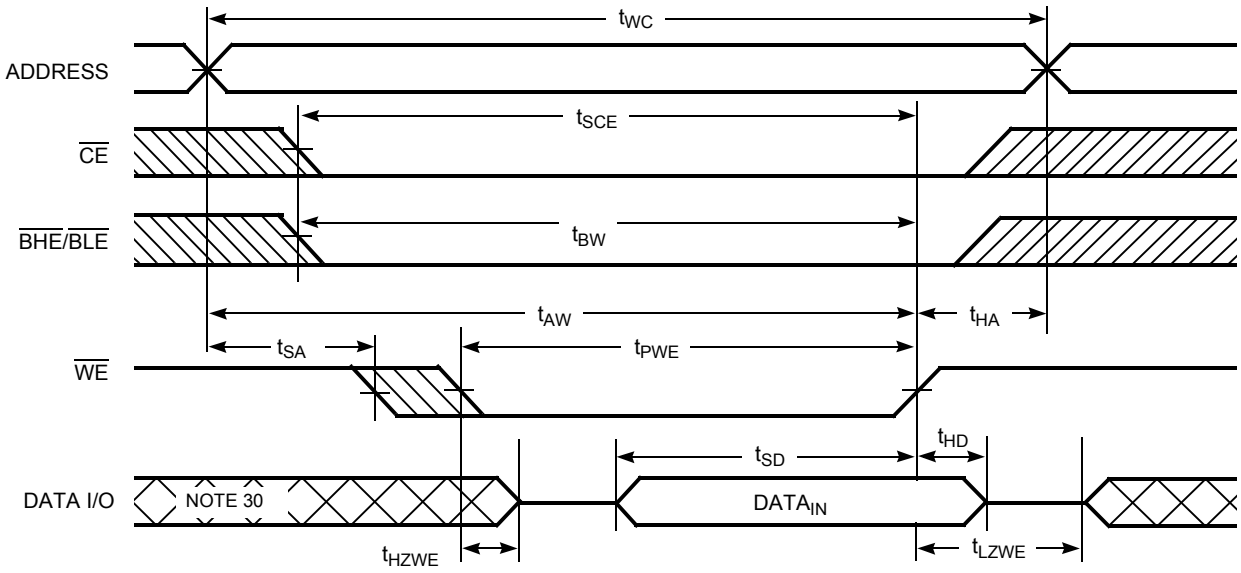
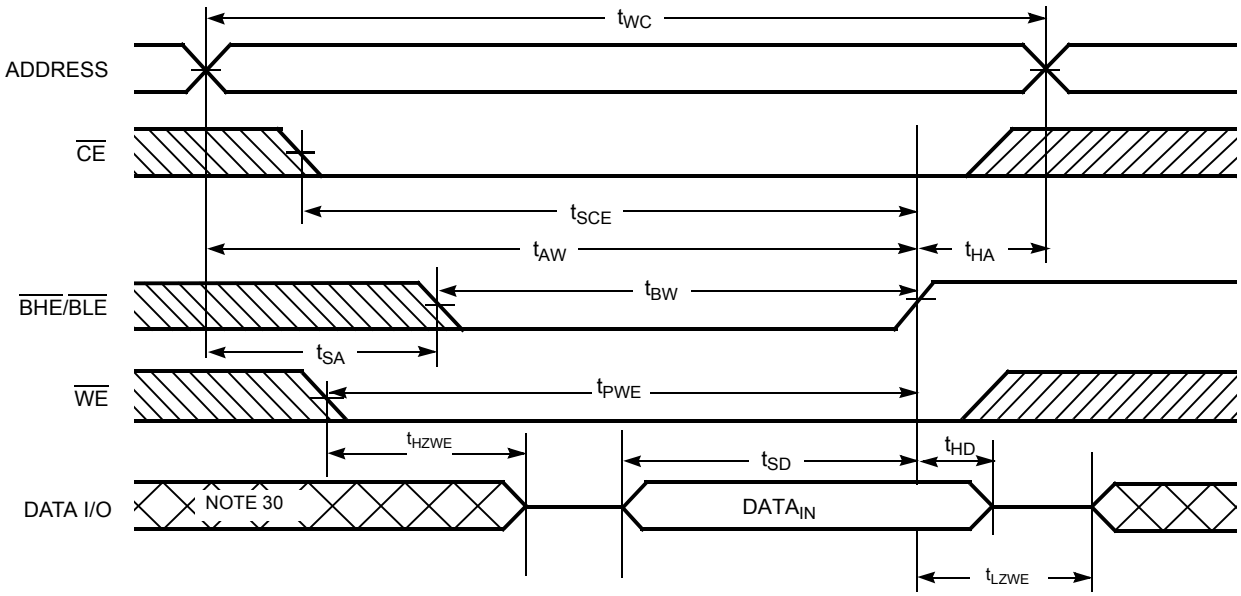


Figure 9. Write Cycle No. 4 (BHE/BLE Controlled, OE LOW) [28]



Notes
28. If CE goes HIGH simultaneously with WE = V_{IH}, the output remains in a high impedance state.
29. The minimum write cycle pulse width should be equal to the sum of t_{HZWE} and t_{SD}.
30. During this period, the I/Os are in output state. Do not apply input signals.

Truth Table

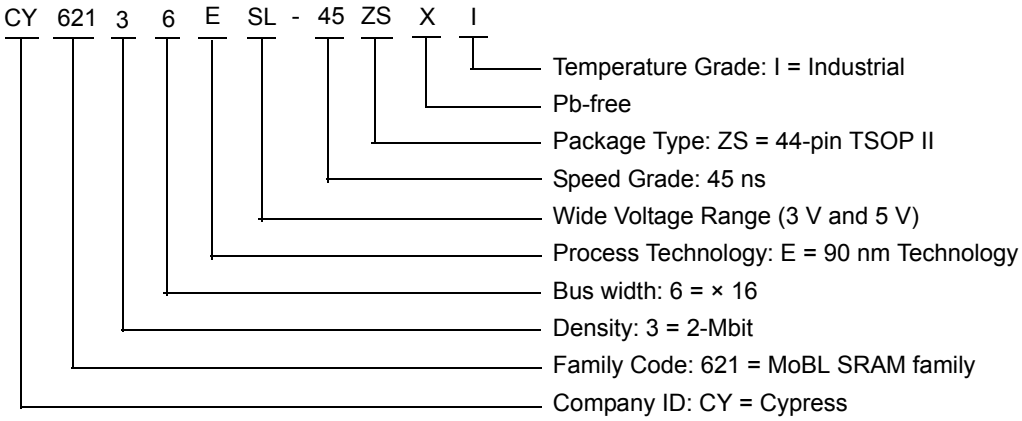
$\overline{CE}$ [31]	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X[31]	X[31]	High Z	Deselect/power-down	Standby (I_{SB})
L	X	X	H	H	High Z	Output disabled	Active (I_{CC})
L	H	L	L	L	Data out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data out (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Output disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output disabled	Active (I_{CC})
L	L	X	L	L	Data in (I/O_0–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data in (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data in (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Write	Active (I_{CC})

Note
31. The 'X' (Don't care) state for the Chip enable ($\overline{CE}$) and Byte enables ($\overline{BHE}$ and $\overline{BLE}$) in the truth table refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

Ordering Information

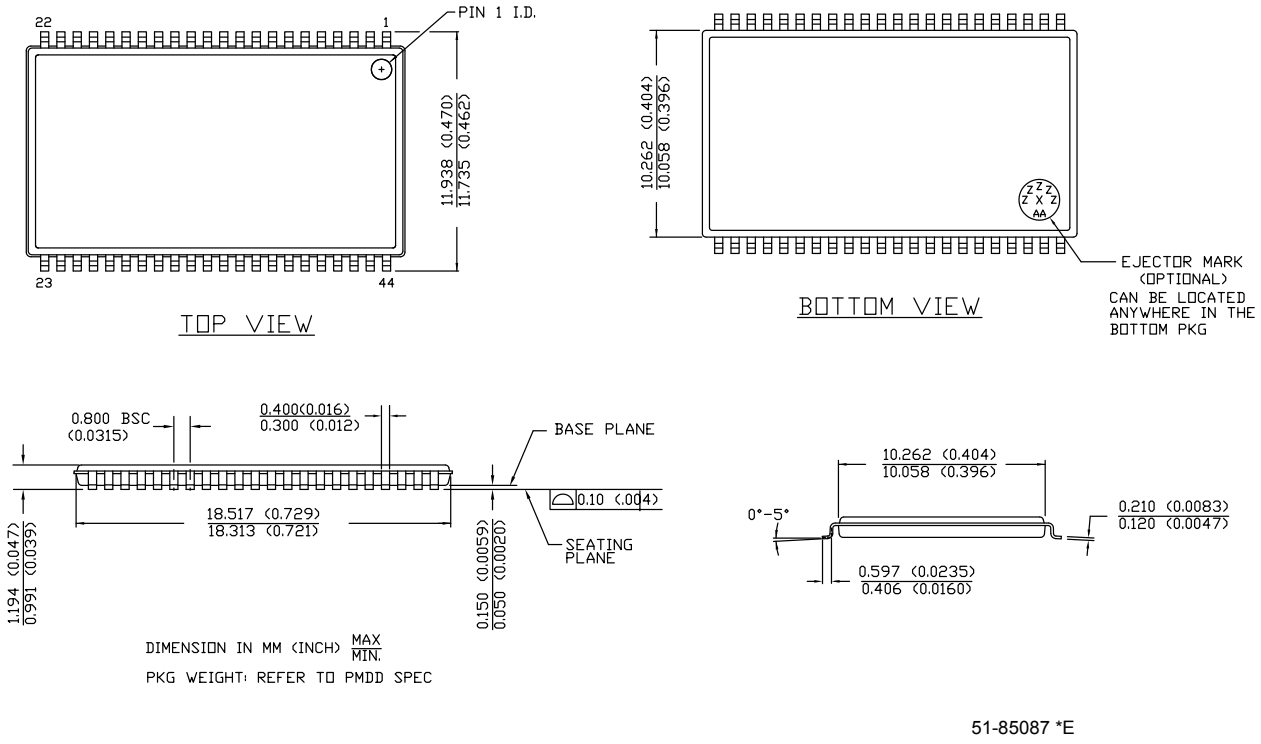
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62136ESL-45ZSXI	51-85087	44-pin TSOP Type II (Pb-free)	Industrial

Ordering Code Definitions



Package Diagram

Figure 10. 44-pin TSOP Z44-II Package Outline, 51-85087



51-85087 *E

Acronyms

Acronym	Description
$\overline{BLE}$	Byte Low Enable
$\overline{BHE}$	Byte High Enable
$\overline{CE}$	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
$\overline{OE}$	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
$\overline{WE}$	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
µA	microampere
µs	microsecond
mA	milliampere
mm	millimeter
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

Document History Page

Document Title: CY62136ESL MoBL®, 2-Mbit (128 K × 16) Static RAM Document Number: 001-48147				
Rev.	**ECN No.**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	2615537	VKN / PYRS	12/03/08	New data sheet.
*A	2718906	VKN	06/15/2009	Post to external web.
*B	2944332	VKN	06/04/2010	Added Contents. Updated Electrical Characteristics: Added Note 9 and referred the same note in I_{SB2} parameter. Updated Switching Characteristics: Added Note 16 and referred the same note in “Parameter” column. Updated Truth Table: Added Note 31 and referred the same note in “$\overline{CE}$”, “$\overline{BHE}$” and “$\overline{BLE}$” columns. Updated Package Diagram. Updated links in Sales, Solutions, and Legal Information.
*C	3126445	RAME	01/03/2011	Changed all table notes to footnotes in all instances across the document. Added Acronyms and Units of Measure. Added Ordering Code Definitions. Updated to new template,
*D	3283711	RAME	06/15/2011	Updated Functional Description (Removed “For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.”). Updated to new template.
*E	3499186	TAVA	01/17/2012	Updated Product Portfolio. Updated Package Diagram.
*F	3874351	NILE	01/18/2013	Updated Package Diagram: spec 51-85087 – Changed revision from *D to *E.
*G	4019657	MEMJ	06/04/2013	Updated Functional Description. Updated Electrical Characteristics: Added one more Test Condition “$4.5 \le V_{CC} \le 5.5$, I_{OH} = –0.1 mA” for V_{OH} parameter and added maximum value corresponding to that Test Condition. Added Note 8 and referred the same note in maximum value for V_{OH} parameter corresponding to Test Condition “$4.5 \le V_{CC} \le 5.5$, I_{OH} = –0.1 mA”.
*H	4100920	VINI	08/21/2013	Updated Switching Characteristics: Added Note 15 and referred the same note in “Parameter” column. Updated to new template.
*I	4540548	VINI	10/28/2014	Updated Maximum Ratings: Referred Notes 4, 5 in “Supply voltage to ground potential”. Updated Electrical Characteristics: Updated Note 8. Updated Switching Characteristics: Added Note 20 and referred the same note in “Write Cycle”. Updated Switching Waveforms: Added Note 29 and referred the same note in Figure 8.
*J	4575393	VINI	11/20/2014	Updated Functional Description: Added “For a complete list of related documentation, click here.” at the end. Updated Switching Waveforms: Updated Figure 5 (Added shading to $\overline{BHE}$/$\overline{BLE}$ in the waveform).

Document History Page (continued)

Document Title: CY62136ESL MoBL®, 2-Mbit (128 K × 16) Static RAM Document Number: 001-48147				
Rev.	**ECN No.**	**Orig. of Change**	**Submission Date**	**Description of Change**
*K	5059123	NILE	12/21/2015	Update Thermal Resistance: Changed value of Θ_{JA} parameter corresponding to 44-pin TSOP II package from 77 °C/W to 57 °C/W. Changed value of Θ_{JC} parameter corresponding to 44-pin TSOP II package from 13 °C/W to 17 °C/W. Updated to new template. Completing Sunset Review.
*L	5978618	AESATMP9	11/29/2017	Updated logo and copyright.

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Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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